

Title (en)  
METHOD OF PRODUCING THICK FILM RESISTOR ELEMENT OF ACCURATE RESISTANCE

Publication  
**EP 0051826 A3 19830720 (EN)**

Application  
**EP 81109284 A 19811029**

Priority  
JP 15579180 A 19801107

Abstract (en)  
[origin: EP0051826A2] In producing a thick film resistor element (12) having a predetermined resistance by the steps of applying a conducting paste to a substrate (10) to form a desirably patterned paste layer and then firing the substrate (10) to sinter the metal powder contained in the applied paste, the paste-applying and firing steps are performed such that the sintered thick film (12) has a provisional resistance lower than, e. g. 70-85% of, the predetermined resistance, and an alternating voltage which is higher than a maximum voltage to be applied to the thick film resistor element (12) in its practical use is applied to the sintered thick film (12) so as to increase its resistance up to the predetermined resistance. By this method the percentage of acceptable products in mass production can be greatly increased.

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**H01C 17/26**; **H01C 17/06**; **H01C 17/22**

IPC 8 full level  
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CPC (source: EP)  
**H01C 17/065** (2013.01); **H01C 17/267** (2013.01)

Citation (search report)  
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